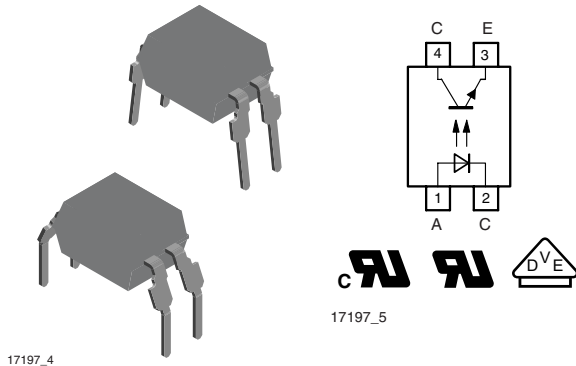


Optocoupler, Phototransistor Output, High Temperature, 110 °C, Rated



DESCRIPTION

The TCET1110, TCET1110G consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4 pin plastic dual inline package.

AGENCY APPROVALS

- UL1577, file no. E52744, double protection
- BSI: EN 60065:2002, EN 60950:2000
- DIN EN 60747-5-5 (VDE 0884)
- FIMKO

FEATURES

- CTR offered in 9 groups
- Isolation materials according to UL 94 V-O
- Pollution degree 2 (DIN/VDE 0110/resp. IEC 60664)
- Climatic classification 55/100/21 (IEC 60068 part 1)
- Special construction: therefore, extra low coupling capacity of typical 0.2 pF, high common mode rejection
- Low temperature coefficient of CTR
- Temperature range - 40 °C to + 110 °C
- Rated impulse voltage (transient overvoltage) $V_{IOTM} = 6 \text{ kV}_{peak}$
- Isolation test voltage (partial discharge test voltage) $V_{pd} = 1.6 \text{ kV}$
- Rated isolation voltage (RMS includes DC) $V_{IOWM} = 600 \text{ V}_{RMS}$
- Rated recurring peak voltage (repetitive) $V_{IORM} = 848 \text{ V}_{peak}$
- Creepage current resistance according to VDE 0303/ IEC 60112 comparative tracking index: CTI ≥ 175
- Thickness through insulation $\geq 4 \text{ mm}$
- External creepage distance $> 8 \text{ mm}$
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

- for appl. class I - IV at mains voltage $\leq 300 \text{ V}$
- for appl. class I - III at mains voltage $\leq 600 \text{ V}$ according to DIN EN 60747-5-5 (VDE 0884), suitable for:
 - Switch-mode power supplies
 - Line receiver
 - Computer peripheral interface
 - Microprocessor system interface



TCET1110, TCET1110G

Optocoupler, Phototransistor Output, Vishay Semiconductors
High Temperature, 110 °C, Rated

ORDER INFORMATION

PART	REMARKS
TCET1110	CTR 50 to 600 %, DIP-4
TCET1111	CTR 40 % to 80 %, DIP-4
TCET1112	CTR 63 % to 125 %, DIP-4
TCET1113	CTR 100 % to 200 %, DIP-4
TCET1114	CTR 160 % to 320 %, DIP-4
TCET1115	CTR 50 % to 150 %, DIP-4
TCET1116	CTR 100 % to 300 %, DIP-4
TCET1117	CTR 80 % to 160 %, DIP-4
TCET1118	CTR 130 % to 260 %, DIP-4
TCET1119	CTR 200 % to 400 %, DIP-4
TCET1110G	CTR 50 % to 600 %, DIP-4
TCET1111G	CTR 40 % to 80 %, DIP-4
TCET1112G	CTR 63 % to 125 %, DIP-4
TCET1113G	CTR 100 % to 200 %, DIP-4
TCET1114G	CTR 160 % to 320 %, DIP-4
TCET1115G	CTR 50 % to 150 %, DIP-4
TCET1116G	CTR 100 % to 300 %, DIP-4
TCET1117G	CTR 80 % to 160 %, DIP-4
TCET1118G	CTR 130 % to 260 %, DIP-4
TCET1119G	CTR 200 % to 400 %, DIP-4

Note

4 pin = single channel

G = lead form 10.16 mm; G is not marked on the body

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu s$	I_{FSM}	1.5	A
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10 ms$	I_{CM}	100	mA
COUPLER				
Isolation test voltage (RMS)	$t = 1 min$	V_{ISO}	5000	V_{RMS}
Operating ambient temperature range		T_{amb}	- 40 to + 110	°C
Storage temperature range		T_{stg}	- 55 to + 125	°C
Soldering temperature ⁽²⁾	2 mm from case, $\leq 10 s$	T_{sld}	260	°C

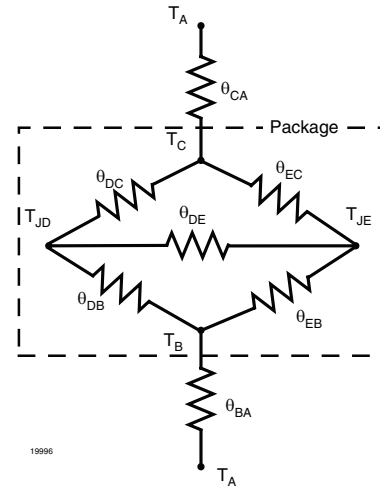
Notes

⁽¹⁾ $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to wave profile for soldering conditions for through hole devices (DIP).

THERMAL CHARACTERISTICS (1)			
PARAMETER	SYMBOL	VALUE	UNIT
LED power dissipation	P_{diss}	70	mW
Output power dissipation	P_{diss}	70	mW
Maximum LED junction temperature	$T_{jmax.}$	125	°C
Maximum output die junction temperature	$T_{jmax.}$	125	°C
Thermal resistance, junction emitter to board	θ_{EB}	173	°C/W
Thermal resistance, junction emitter to case	θ_{EC}	149	°C/W
Thermal resistance, junction detector to board	θ_{DB}	111	°C/W
Thermal resistance, junction detector to case	θ_{DC}	127	°C/W
Thermal resistance, junction emitter to junction detector	θ_{ED}	173	°C/W
Thermal resistance, board to ambient (2)	θ_{BA}	197	°C/W
Thermal resistance, case to ambient (2)	θ_{CA}	4041	°C/W



Note

(1) The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's "Thermal Characteristics of Optocouplers" application note.

(2) For 2 layer FR4 board (4" x 3" x 0.062").

ELECTRICAL CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		50		pF
OUTPUT						
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100 \text{ }\mu\text{A}$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0, E = 0$	I_{CEO}		10	100	nA
COUPLER						
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \text{ }\Omega$	f_c		110		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	C_k		0.6		pF

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.



TCET1110, TCET1110G

Optocoupler, Phototransistor Output, Vishay Semiconductors
High Temperature, 110 °C, Rated

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$V_{CE} = 5\text{ V}, I_F = 1\text{ mA}$	TCET1111 TCET1111G	CTR	13	30		%
		TCET1112 TCET1112G	CTR	22	45		%
		TCET1113 TCET1113G	CTR	34	70		%
		TCET1114 TCET1114G	CTR	56	90		%
	$V_{CE} = 5\text{ V}, I_F = 5\text{ mA}$	TCET1110 TCET1110G	CTR	50		600	%
		TCET1115 TCET1115G	CTR	50		150	%
		TCET1116 TCET1116G	CTR	100		300	%
		TCET1117 TCET1117G	CTR	80		160	%
		TCET1118 TCET1118G	CTR	130		260	%
		TCET1119 TCET1119G	CTR	200		400	%
	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}$	TCET1111 TCET1111G	CTR	40		80	%
		TCET1112 TCET1112G	CTR	63		125	%
		TCET1113 TCET1113G	CTR	100		200	%
		TCET1114 TCET1114G	CTR	160		320	%

MAXIMUM SAFETY RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward current		I_F			130	mA
OUTPUT						
Power dissipation		P_{diss}			265	mW
COUPLER						
Rated impulse voltage		V_{IOTM}			6	kV
Safety temperature		T_{si}			150	°C

Note

According to DIN EN 60747-5-5 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, $t_{test} = 1\text{ s}$	V_{pd}	1.6			kV
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60\text{ s}, t_{test} = 10\text{ s},$ (see figure 2)	V_{IOTM}	8			kV
		V_{pd}	1.3			kV
Insulation resistance	$V_{IO} = 500\text{ V}$	R_{IO}	10^{12}			Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ °C}$	R_{IO}	10^{11}			Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 150\text{ °C}$ (construction test only)	R_{IO}	10^9			Ω

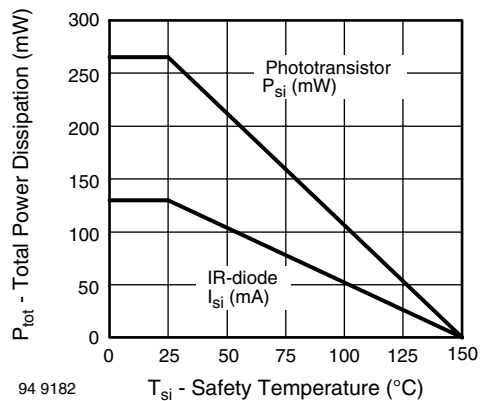


Fig. 1 - Derating Diagram

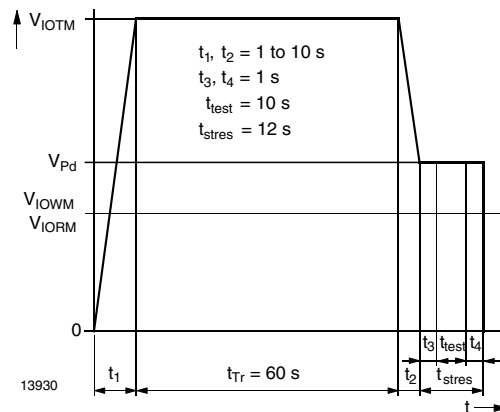


Fig. 2 - Test Pulse Diagram for Sample Test according to
DIN EN 60747-5-5/DIN EN 60747-; IEC 60747

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP.	MAX	UNIT
Delay time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_d		3		μs
Rise time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_r		3		μs
Fall time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_f		4.7		μs
Storage time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_s		0.3		μs
Turn-on time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_{on}		6		μs
Turn-off time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_{off}		5		μs
Turn-on time	$V_S = 5 \text{ V}$, $I_F = 10 \text{ mA}$, $R_L = 1 \text{ k}\Omega$, (see figure 4)	t_{on}		9		μs
Turn-off time	$V_S = 5 \text{ V}$, $I_F = 10 \text{ mA}$, $R_L = 1 \text{ k}\Omega$, (see figure 4)	t_{off}		10		μs

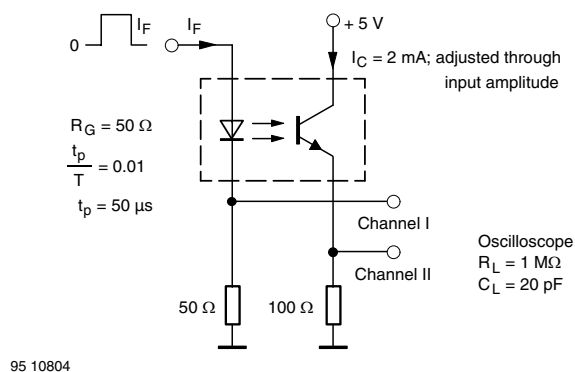


Fig. 3 - Test Circuit, Non-Saturated Operation

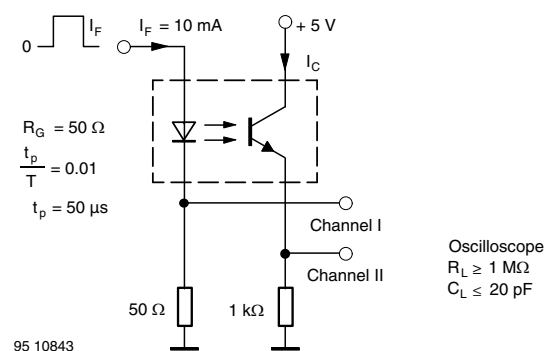


Fig. 4 - Test Circuit, Saturated Operation

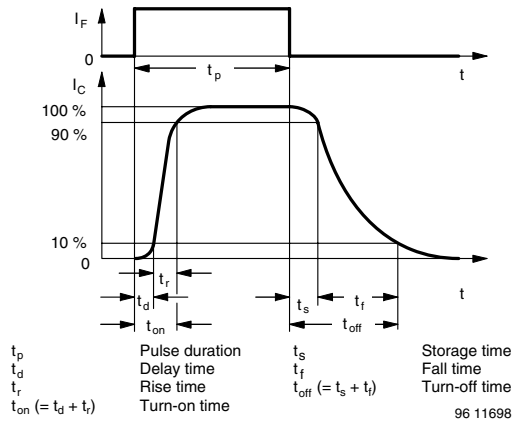


Fig. 5 - Switching Times

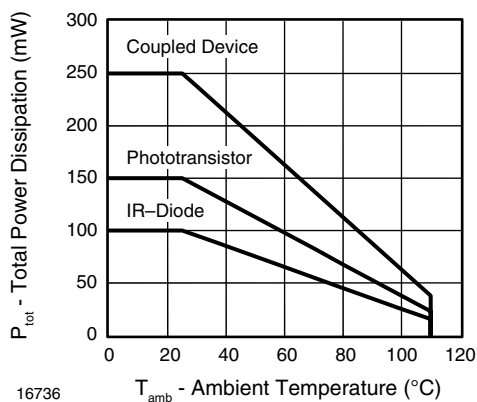
TYPICAL CHARACTERISTICS
 $T_{amb} = 25\text{ °C}$, unless otherwise specified


Fig. 6 Total Power Dissipation vs. Ambient Temperature

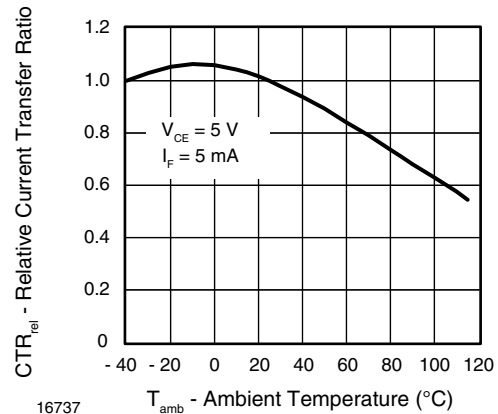


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

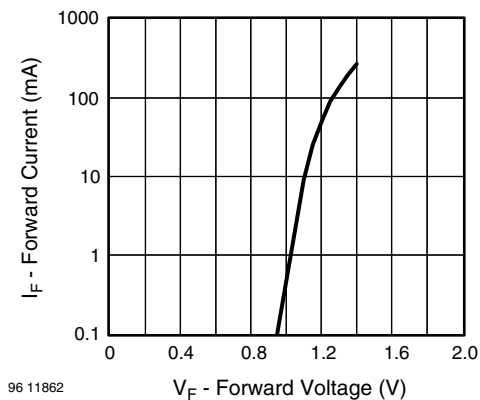


Fig. 7 - Forward Current vs. Forward Voltage

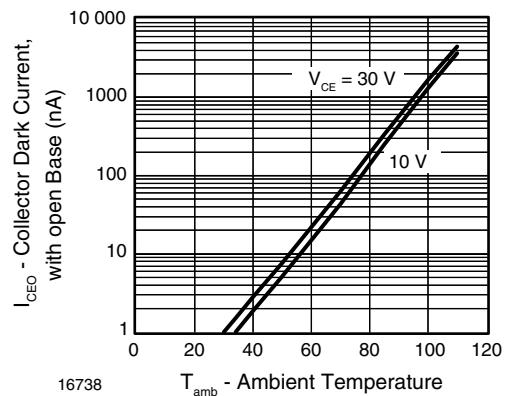


Fig. 9 - Collector Dark Current vs. Ambient Temperature

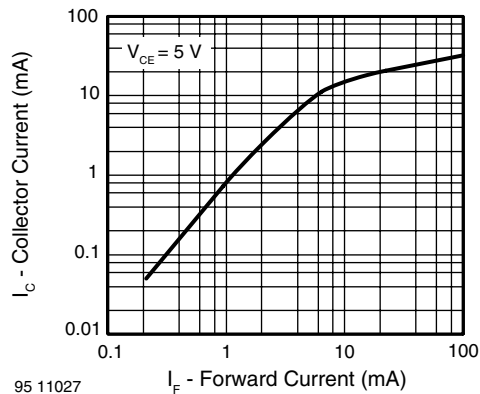


Fig. 10 - Collector Current vs. Forward Current

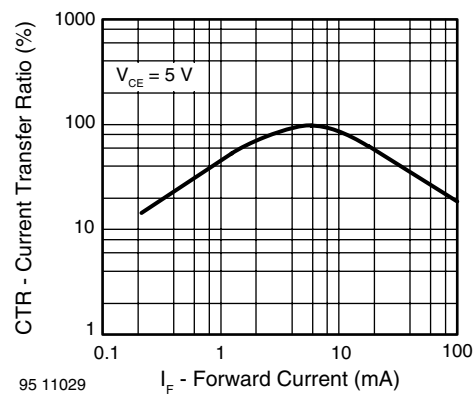


Fig. 13 - Current Transfer Ratio vs. Forward Current

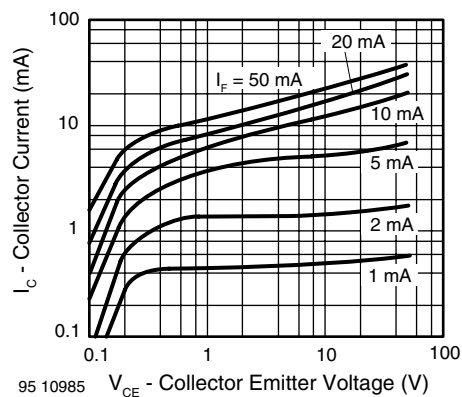


Fig. 11 - Collector Current vs. Collector Emitter Voltage

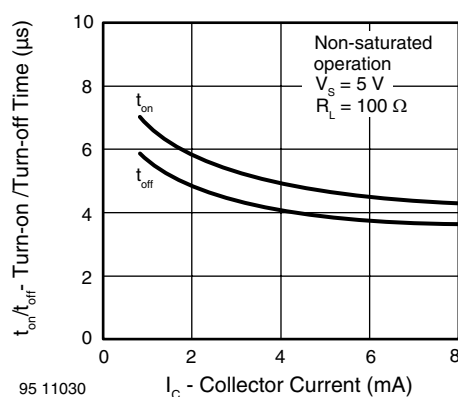


Fig. 14 - Turn-on/off Time vs. Collector Current

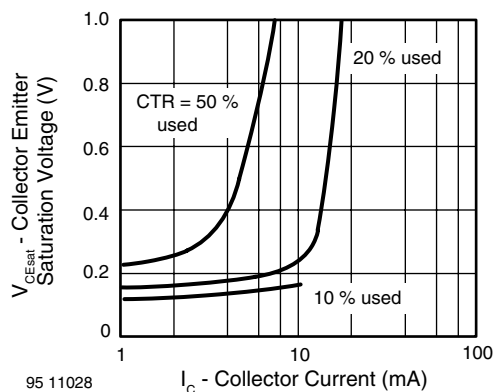


Fig. 12 - Collector Emitter Saturation Voltage vs. Collector Current

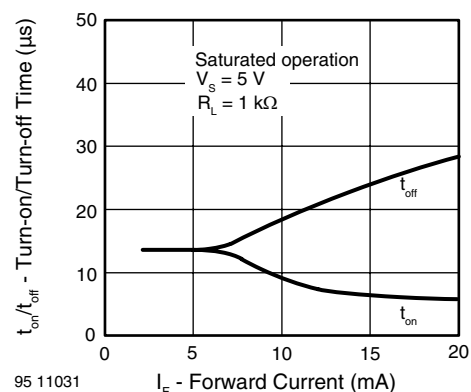


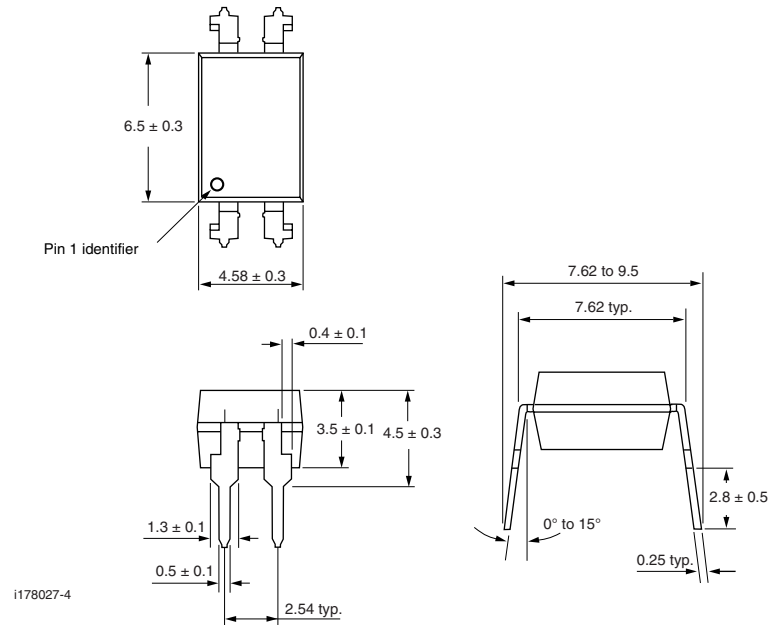
Fig. 15 - Turn-on/off Time vs. Forward Current



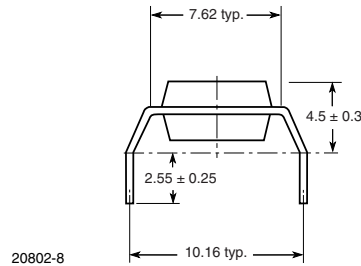
TCET1110, TCET1110G

Optocoupler, Phototransistor Output, Vishay Semiconductors
High Temperature, 110 °C, Rated

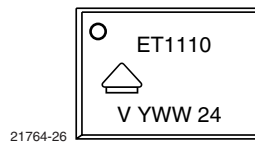
PACKAGE DIMENSIONS in millimeters



TCET1110G type



PACKAGE MARKING





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